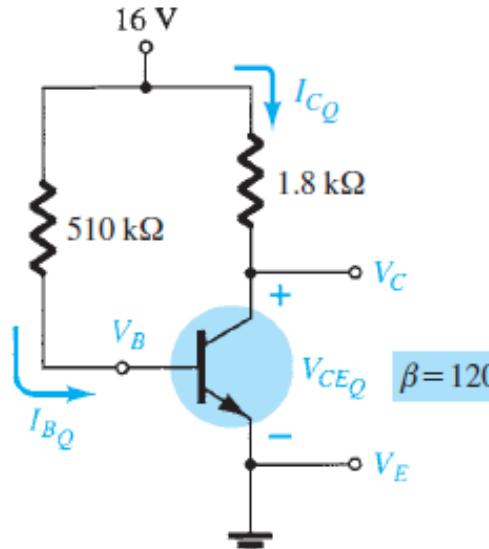


Tutorial Sheet No. - 4

[1] For the fixed-bias configuration of Fig. 1, determine a. I_{BQ} . b. I_{CQ} . c. V_{CEQ} . d. V_C . e. V_B . f. V_E .	
	Fig. 1

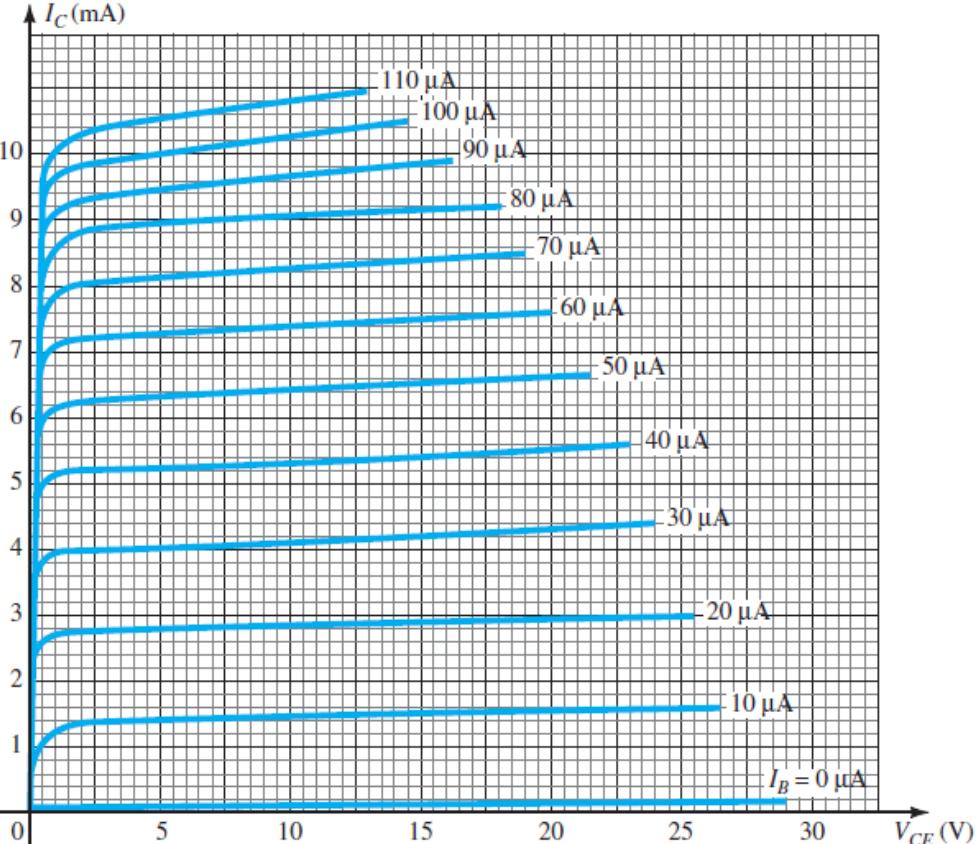
[2]	<p>Given the BJT transistor characteristics of Fig. 2 :</p> <ol style="list-style-type: none"> Draw a load line on the characteristics determined by $E = 21 \text{ V}$ and $R_C = 3 \text{ k}\Omega$ for a fixed-bias configuration. Choose an operating point midway between cutoff and saturation. Determine the value of R_B to establish the resulting operating point. What are the resulting values of I_{CQ} and V_{CEQ}? What is the value of β at the operating point? What is the value of α defined by the operating point? What is the saturation current ($I_{C_{sat}}$) for the design? Sketch the resulting fixed-bias configuration. What is the dc power dissipated by the device at the operating point? What is the power supplied by V_{CC}? Determine the power dissipated by the resistive elements by taking the difference between the results of parts (h) and (i). 
[3]	<p>If the base resistor of Fig. 1 is increased to 910 kohm, find the new Q-point and resulting values of I_{CQ} and V_{CEQ}.</p>
[4]	<p>Given the information provided in Fig. 3 , determine:</p> <ol style="list-style-type: none"> R_C . R_E .

Fig. 2

- c. R_B .
- d. V_{CE} .
- e. V_B .

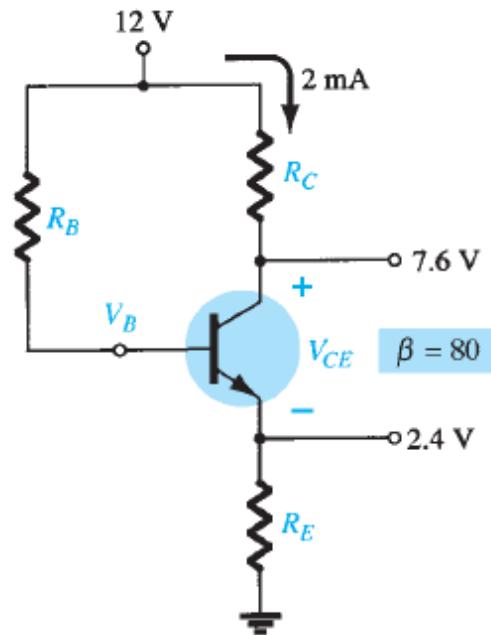


Fig. 3